L Number	Hits	Search Text	DB	Tim stamp
21	116	(acc leration near s ns r) and 257/415	USPAT;	2004/01/12
			US-PGPUB;	09:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	28	(acceleration near sensor).clm. and 257/415	USPAT;	2004/01/12
			US-PGPUB;	09:40
}			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	21157	acceleration adj sensor	USPAT;	2004/01/06
			US-PGPUB;	11:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2028	(acceleration adj sensor).clm.	USPAT;	2004/01/06
			US-PGPUB;	11:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	177	(acceleration adj sensor).clm. and		2004/01/06
_	17.4	beam.clm.	USPAT;	}
		Deam.Cilli.	US-PGPUB;	11:12
			EPO; JPO;	
}			DERWENT;	
ļ	_	(IBM_TDB	0004/04/00
-	5	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
		beam.clm. and (piezoresistor).clm.	US-PGPUB;	11:13
			EPO; JPO;	
			DERWENT;	
	•		IBM_TDB	0004/04/00
•	0	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
		beam.clm. and (piezoresistor).clm. and (tft	US-PGPUB;	11:13
		or (thin near film near transistor)).clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	0	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
		(piezoresistor).clm. and (tft or (thin near	US-PGPUB;	11:13
		film near transistor)).clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	0	(acceleration adj sensor).clm. and (tft or	USPAT;	2004/01/06
		(thin near film near transistor)).clm.	US-PGPUB;	11:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(acceleration adj sensor).clm. and (tft or	USPAT;	2004/01/06
		(thin near film near transistor))	US-PGPUB;	11:17
	ļ		EPO; JPO;	
			DERWENT;	
}			IBM_TDB	

	26	(ac I rati n adj sensor) and (tft or (thin	USPAT;	2004/01/06
		n ar film near transist r))	US-PGPUB;	11:17
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
	3	(acceleration adj sensor) and (tft or (thin	USPAT;	2004/01/06
	3	near film near transistor)) and (piezo or	US-PGPUB;	11:17
		piezoresistor)	EPO; JPO;	
		p	DERWENT;	
			IBM_TDB	
\ <u>_</u>	165494	sensor.clm.	USPAT;	2004/01/06
			US-PGPUB;	11:17
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	259	sensor.clm. and (tft or (thin near film near	USPAT;	2004/01/06
		transistor)).clm.	US-PGPUB;	11:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	sensor.clm. and (tft or (thin near film near	USPAT;	2004/01/06
		transistor)).clm. and piezoresistor.clm.	US-PGPUB;	11:19
		,,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(acceleration near sensor).clm. and (tft or	USPAT;	2004/01/06
		(thin near film near transistor)).clm.	US-PGPUB;	11:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6870	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
			US-PGPUB;	11:20
			EPO; JPO;	
			DERWENT;	
}			IBM_TDB	
-	259	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm.	US-PGPUB;	11:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
	1	and sensor.clm. and beam.clm.	US-PGPUB;	11:21
			EPO; JPO;	
	}		DERWENT;	
			IBM_TDB	
-	15	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:22
		sensor.ab.	EPO; JPO;	
			DERWENT;	
L	<u></u>		IBM_TDB	

				
-	9	(tft or (thin n ar film n ar transist r)).clm.	USPAT;	2004/01/06
		and sens r.clm. and beam.clm. and	US-PGPUB;	11:22
		s ns r.ab. and substrat .clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:22
+		sensor.ab. and substrate.clm. and (tft or	EPO; JPO;	
		(thin near film near transistor)).clm.	DERWENT;	
			IBM_TDB	
] -	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:22
		sensor.ab. and substrate.clm. and (tft or	EPO; JPO;	
		(thin near film near transistor)).ab.	DERWENT;	
[IBM_TDB	
-	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:23
		sensor.ab. and substrate.clm. and (piezo or	EPO; JPO;	
		piezoelectric or piezoresistor)	DERWENT;	
ĺ			IBM_TDB	
-	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:23
		sensor.ab. and substrate.clm. and (piezo or	EPO; JPO;	
		piezoelectric or piezoresistor).clm.	DERWENT;	
		(454 (45	IBM_TDB	0004/04/00
-	1	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and sensor.ab. and	US-PGPUB;	11:23
		substrate.clm. and (piezo or piezoelectric or piezoresistor).clm.	EPO; JPO; DERWENT;	
		or prezoresistor, citi.	IBM_TDB	
}	2099	(acceleration near sensor).clm.	USPAT;	2004/01/06
	2000	(acceleration near sensor).cmi.	US-PGPUB;	11:24
			EPO; JPO;	11.27
			DERWENT;	
			IBM_TDB	
-	0	(acceleration near sensor).clm. and (tft or	USPAT;	2004/01/06
		(thin near film near transistor)).clm.	US-PGPUB;	11:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(acceleration near sensor).clm. and (tft or	USPAT;	2004/01/06
		(thin near film near transistor))	US-PGPUB;	11:24
			EPO; JPO;	
			DERWENT;	}
			IBM_TDB	
-	201	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm.	US-PGPUB;	11:24
			EPO; JPO;	
			DERWENT;	
		<u></u>	IBM_TDB	

•	201	(acc leration n ars ns r).clm. and (piez	USPAT;	2004/01/06
		or piez electric r piezoresistor).clm.	U -PGPUB;	11:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm. and (thin near	EPO; JPO;	
		film)	DERWENT;	
			IBM_TDB	
•	4	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
H	1	or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm. and ((thin near	EPO; JPO;	
		film) or tft)	DERWENT;	
			IBM_TDB	
-	1	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
		(cantilever or beam).clm. and ((thin near	EPO; JPO;	
		film) or tft).clm.	DERWENT;	
			IBM_TDB	
•	0	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
		(cantilever or beam).clm. and (tft).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	0	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
,		(cantilever or beam).clm. and (tft)	EPO; JPO;	
			DERWENT;	
	4	(cancar) alm and (niora au niora-la-tria au	IBM_TDB	2004/04/06
-	4	(sensor).clm. and (piezo or piezoelectric or	USPAT;	2004/01/06
		piezoresistor).clm. and (cantilever or beam).clm. and (tft)	US-PGPUB; EPO; JPO;	11:32
		beam, cin. and (tit)	•	
			DERWENT;	
_	2099	(acceleration near sensor).clm.	IBM_TDB USPAT;	2004/01/06
		(about ation near sensor), citil.	US-PGPUB;	11:32
	1		EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	56	(acceleration near sensor).clm. and	USPAT;	2004/01/06
		(insulating or dielectric).clm. and	US-PGPUB;	11:33
		substrate.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	0	(accolorati n near concer) olm and	USPAT;	2004/01/06
-	•	(accelerati n near sensor).clm. and		
		(insulating or dielectric).clm. and	US-PGPUB;	11:33
		substrate.clm. and tft	EPO; JPO;	
			DERWENT;	
			IBM_TDB	G00 4/0 4/00
-	23	(acceleration near sensor).clm. and	USPAT;	2004/01/06
		(insulating or dielectric).clm. and	US-PGPUB;	11:33
		substrate.clm. and (tft or (thin near film))	EPO; JPO;	
i			DERWENT;	
			IBM_TDB	
-	0	(acceleration near sensor).clm. and	USPAT;	2004/01/06
		(insulating or dielectric).clm. and	US-PGPUB;	11:34
		substrate.clm. and (tft or (thin near film	EPO; JPO;	
		near transistor))	DERWENT;	
			IBM_TDB	
-	4380	(insulating or dielectric).clm. and	USPAT;	2004/01/06
1		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm.	EPO; JPO;	
			DERWENT;	
:			IBM_TDB	
-	3	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm. and piezoresistor.clm.\	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm. and piezoresistor.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm. and piezoresistor.clm. and	EPO; JPO;	
		(acceleration near sensor).clm.	DERWENT;	
			IBM_TDB	
\	O	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:36
	1	beam).clm. and (piezo or piezoelectric or	EPO; JPO;	
		piezoresistor).clm. and (acceleration near	DERWENT;	
]	sensor).cim.	IBM_TDB	
-	31	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:36
		(acceleration near sensor).clm.	EPO; JPO;	
			DERWENT;	
	[IBM TDB	
-	21	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:39
	}	(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab.	DERWENT;	
		, and the second	IBM_TDB	
ــــــــــــــــــــــــ ــــــــــــ	 			<u></u>

	42	(appellant to the production of the state of	HCDAT.	2004/04/06
-	13	(cantilev r r beam).clm. and (piezo r	USPAT;	2004/01/06
		piezoel ctric r pi zoresistor).clm. and	US-PGPUB;	11:39
		(acceleration near sens r).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
	6	beam.clm.	IBM_TDB	2004/01/06
-		(cantilever or beam).clm. and (piezo or	USPAT;	11:40
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11140
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm.	IBM_TDB	2004/04/06
-	0	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:40
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and	IBM_TDB	
}		(insulating or dielectric).clm.	HODAT	2004/04/00
-	1	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
}		beam.clm. and substrate.clm. and (thin	IBM_TDB	
	0	near film).clm.	HODAT	2004/04/00
-		(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
	ļ	piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and beam.clm. and substrate.clm. and (thin	DERWENT;	
		near film).clm. and (pcb or printed).clm.	IBM_TDB	
1_	0	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	11,42
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and (pcb or	IBM_TDB	
		printed).clm.	10111_100	
-	6	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	11.42
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm.	IBM TDB	
-	4	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:43
		(acceleration near sensor).clm. and	EPO; JPO;	
}		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and	IBM TDB	
		(cantilever or cantilevered).clm.		
-	4	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:45
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.cim. and substrate.clm. and	IBM_TDB	
	}	(cantilever or cantilevered).clm. and		
		(cantil v r rcantilever d).ab.		
	<u> </u>	<u> </u>		